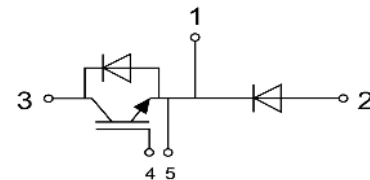


$V_{CES} = 1200V$
$I_C = 200A$ at $T_C = 80^\circ C$
$t_{SC} \geq 10\mu sec$
$V_{CE(ON)} = 1.90V$ at $I_C = 200A$

High-Side Chopper IGBT with Low-Side Diode
POWIR 62™ Package



Applications:

- Industrial Motor Drive
- Uninterruptible Power Supply
- Welding and Cutting Machine
- Switched Mode Power Supply

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High Efficiency in a Wide Range of Applications
RBSOA Tested	Rugged Transient Performance
10 μsec Short Circuit Safe Operating Area	
POWIR 62™ Package	Industry Standard
Lead Free	RoHS Compliant, Environmental Friendly

Base Part Number	Package Type	Standard Pack	Quantity	Orderable Part Number
IRG7T200CH12B	POWIR 62™	Box	45	IRG7T200CH12B

Absolute Maximum Ratings of IGBT

V_{CES}	Collector to Emitter Voltage	1200	V
V_{GES}	Continuous Gate to Emitter Voltage	±20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C$	200 A
		$T_C = 25^\circ C$	390 A
I_{CM}	Pulse Collector Current	$T_J = 175^\circ C$	400 A
P_D	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C, T_J = 175^\circ C$	1060 W
T_J	Maximum IGBT Junction Temperature	175	°C
T_{JOP}	Maximum Operating Junction Temperature Range	-40 to +150	°C
T_{stg}	Storage Temperature	-40 to +125	°C

Electrical Characteristics of IGBT at $T_J = 25^\circ\text{C}$ (Unless Otherwise Specified)

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$V_{(BR)CES}$	Collector to Emitter Breakdown Voltage	1200			V	$V_{GE} = 0V, I_C = 2mA$	
$V_{GE(th)}$	Gate Threshold Voltage	5.0	5.8	6.5	V	$I_C = 10mA, V_{CE} = V_{GE}$	
$V_{CE(ON)}$	Collector to Emitter Saturation Voltage		1.90	2.20	V	$T_J = 25^\circ\text{C}$	$I_C = 200A, V_{GE} = 15V$
			2.20		V	$T_J = 125^\circ\text{C}$	
I_{CES}	Collector to Emitter Leakage Current			2	mA	$V_{GE} = 0V, V_{CE} = V_{CES}$	
I_{GES}	Gate to Emitter Leakage Current			400	nA	$V_{GE} = \pm 20V, V_{CE} = 0$	
R_{Gint}	Internal Gate Resistance		1.25		Ω		

Switching Characteristics of IGBT

Parameter		Min.	Typ.	Max.	Unit	Test Conditions	
$t_{d(on)}$	Turn-on Delay Time		355		ns	$T_J = 25^\circ\text{C}$	$V_{CC}=600V, I_C = 200A, R_G = 10\Omega, V_{GE}=\pm 15V, \text{Inductive Load}$
			320			$T_J = 125^\circ\text{C}$	
t_r	Rise Time		200		ns	$T_J = 25^\circ\text{C}$	
			210			$T_J = 125^\circ\text{C}$	
$t_{d(off)}$	Turn-off Delay Time		525		ns	$T_J = 25^\circ\text{C}$	
			560			$T_J = 125^\circ\text{C}$	
t_f	Fall Time		170		ns	$T_J = 25^\circ\text{C}$	
			190			$T_J = 125^\circ\text{C}$	
E_{on}	Turn-on Switching Loss		24.6		mJ	$T_J = 25^\circ\text{C}$	
			33.0			$T_J = 125^\circ\text{C}$	
E_{off}	Turn-off Switching Loss		12.7		mJ	$T_J = 25^\circ\text{C}$	
			17.2			$T_J = 125^\circ\text{C}$	
Q_g	Total Gate Charge		1800		nC	$T_J = 25^\circ\text{C}$	
C_{ies}	Input Capacitance		22.5		nF	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz, T_J = 25^\circ\text{C}$	
C_{oes}	Output Capacitance		1.56				
C_{res}	Reverse Transfer Capacitance		0.94				
RBSOA	Reverse Bias Safe Operating Area	Trapezoid				$I_C = 400A, V_{CC} = 960V, V_P = 1200V, R_G = 15\Omega, V_{GE} = +15V \text{ to } 0V, T_J = 150^\circ\text{C}$	
SCSOA	Short Circuit Safe Operating Area	10			μs	$V_{CC} = 600V, V_{GE} = 15V, T_J = 150^\circ\text{C}$	

Absolute Maximum Ratings of Freewheeling Diode

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current, $T_C = 25^\circ\text{C}$	400	A
	Diode Continuous Forward Current, $T_C = 80^\circ\text{C}$	200	
I_{FM}	Pulse Diode Current	400	A

Electrical and Switching Characteristics of Freewheeling Diode

Parameter		Typ.	Max.	Unit	Test Conditions	
V_F	Forward Voltage	2.00	2.70	V	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$, $V_{GE} = 0\text{V}$
		2.20			$T_J = 125^\circ\text{C}$	
I_{rr}	Peak Reverse Recovery Current	70		A	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$, $di/dt = 1100\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$
		110			$T_J = 125^\circ\text{C}$	
Q_{rr}	Reverse Recovery Charge	10.6		μC	$T_J = 25^\circ\text{C}$	
		22.3			$T_J = 125^\circ\text{C}$	
E_{rec}	Reverse Recovery Energy	3.7		mJ	$T_J = 25^\circ\text{C}$	
		8.1			$T_J = 125^\circ\text{C}$	

Absolute Maximum Ratings of Brake-Chopper Diode

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current, $T_C = 25^\circ\text{C}$	400	A
	Diode Continuous Forward Current, $T_C = 80^\circ\text{C}$	200	
I_{FM}	Pulse Diode Current	400	A

Electrical and Switching Characteristics of Brake-Chopper Diode

Parameter		Typ.	Max.	Unit	Test Conditions	
V_F	Forward Voltage	2.00	2.70	V	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$, $V_{GE} = 0\text{V}$
		2.20			$T_J = 125^\circ\text{C}$	
I_{rr}	Peak Reverse Recovery Current	70		A	$T_J = 25^\circ\text{C}$	$I_F = 200\text{A}$, $di/dt = 1100\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$
		110			$T_J = 125^\circ\text{C}$	
Q_{rr}	Reverse Recovery Charge	10.6		μC	$T_J = 25^\circ\text{C}$	
		22.3			$T_J = 125^\circ\text{C}$	
E_{rec}	Reverse Recovery Energy	3.7		mJ	$T_J = 25^\circ\text{C}$	
		8.1			$T_J = 125^\circ\text{C}$	

Module Characteristics

Parameter		Min.	Typ.	Max.	Unit
V _{iso}	Isolation Voltage (All Terminals Shorted), f = 50Hz, 1minute			2500	V
R _{θJC}	Junction-to-Case (IGBT)		0.141		°C/W
R _{θJC}	Junction-to-Case (Freewheeling Diode)		0.204		°C/W
R _{θJC}	Junction-to-Case (Brake-Chopper Diode)		0.204		°C/W
R _{θCS}	Case-To-Sink (Conductive Grease Applied)		0.1		°C/W
M	Power Terminals Screw: M6	3.0		5.0	N·m
M	Mounting Screw: M6	4.0		6.0	N·m
G	Weight		230		g

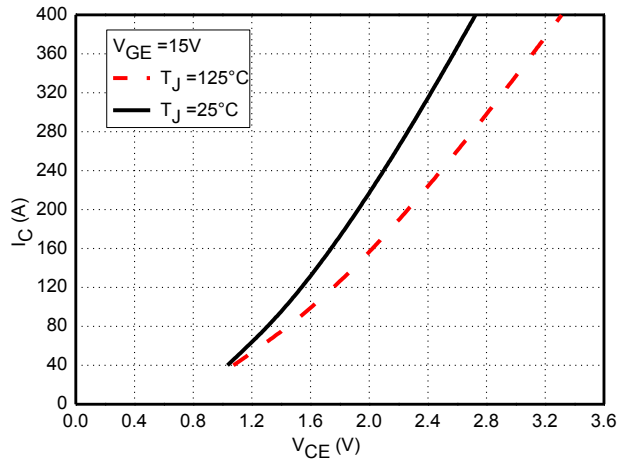


Fig.1 Typical IGBT Saturation Characteristics

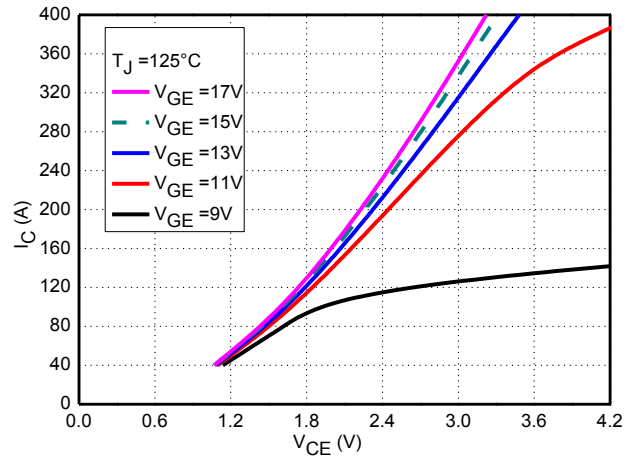


Fig.2 Typical IGBT Output Characteristics

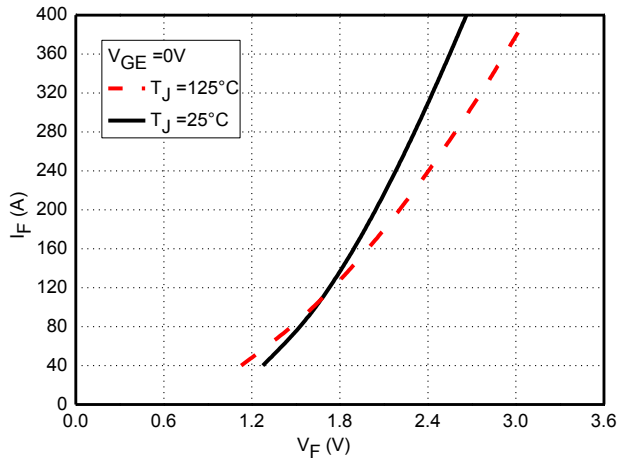


Fig.3 Typical Forward Characteristics, Freewheeling Diode

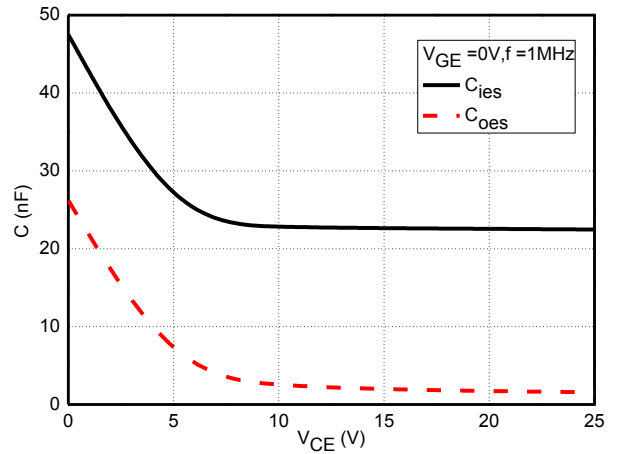


Fig. 4 Typical Capacitance Characteristics

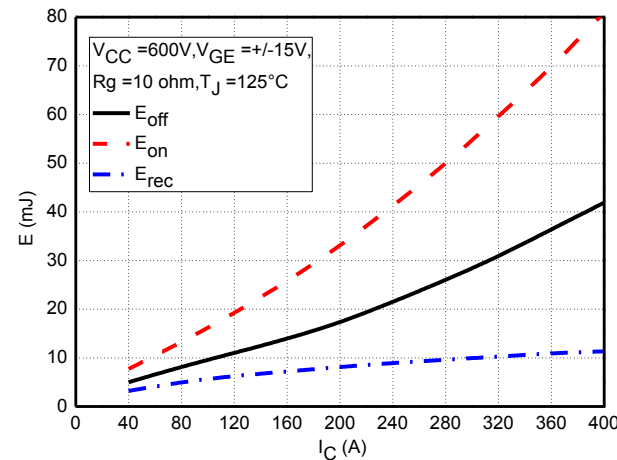


Fig.5 Typical Switching Loss vs. Collector Current

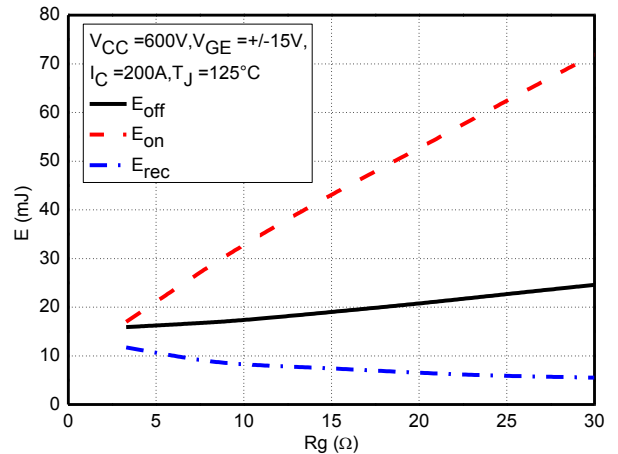


Fig.6 Typical Switching Loss vs. Gate Resistance

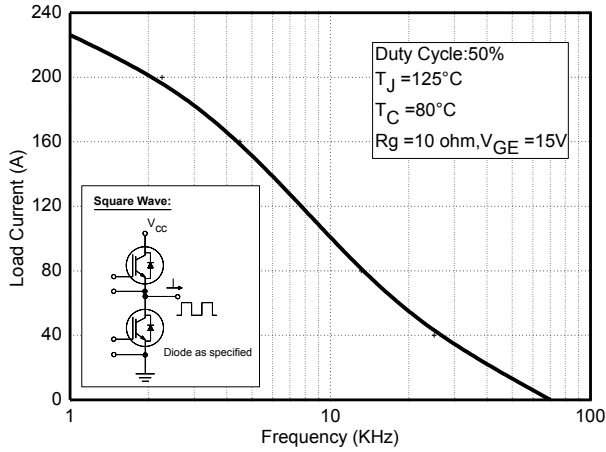


Fig.7 Typical Load Current vs. Frequency

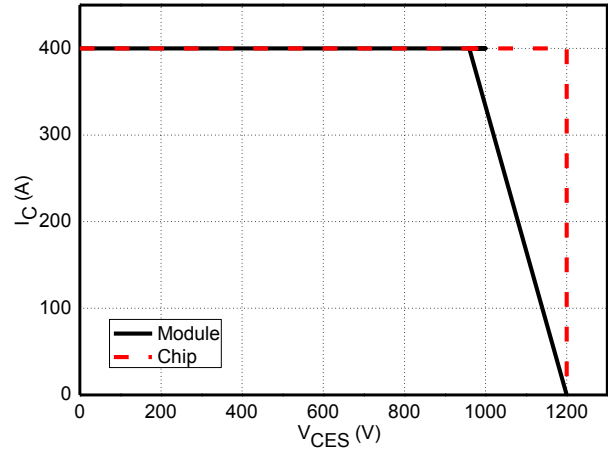


Fig.8 Reverse Bias Safe Operation Area (RBSOA)

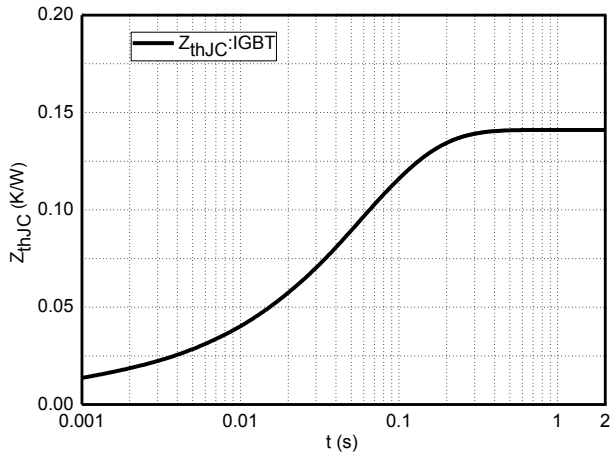


Fig.9 Typical Transient Thermal Impedance (IGBT)

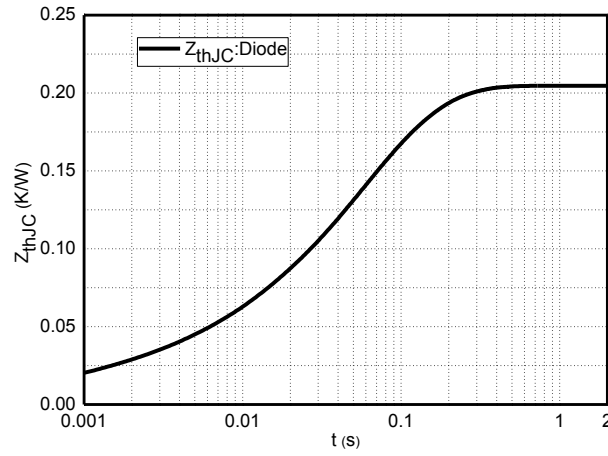


Fig.10 Typical Transient Thermal Impedance (Diode)

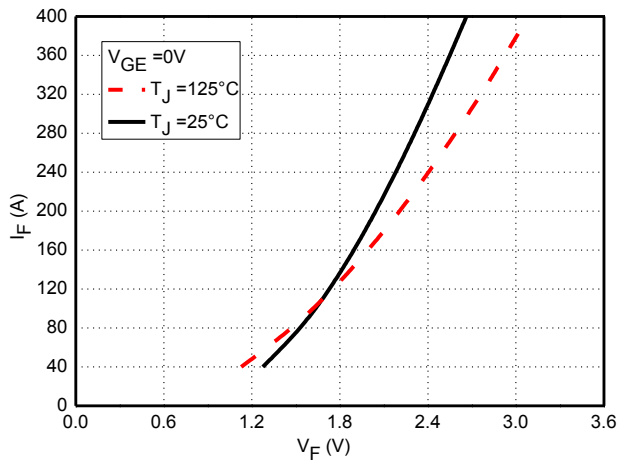
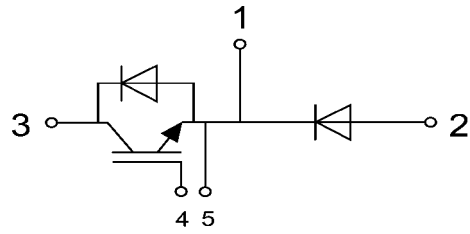


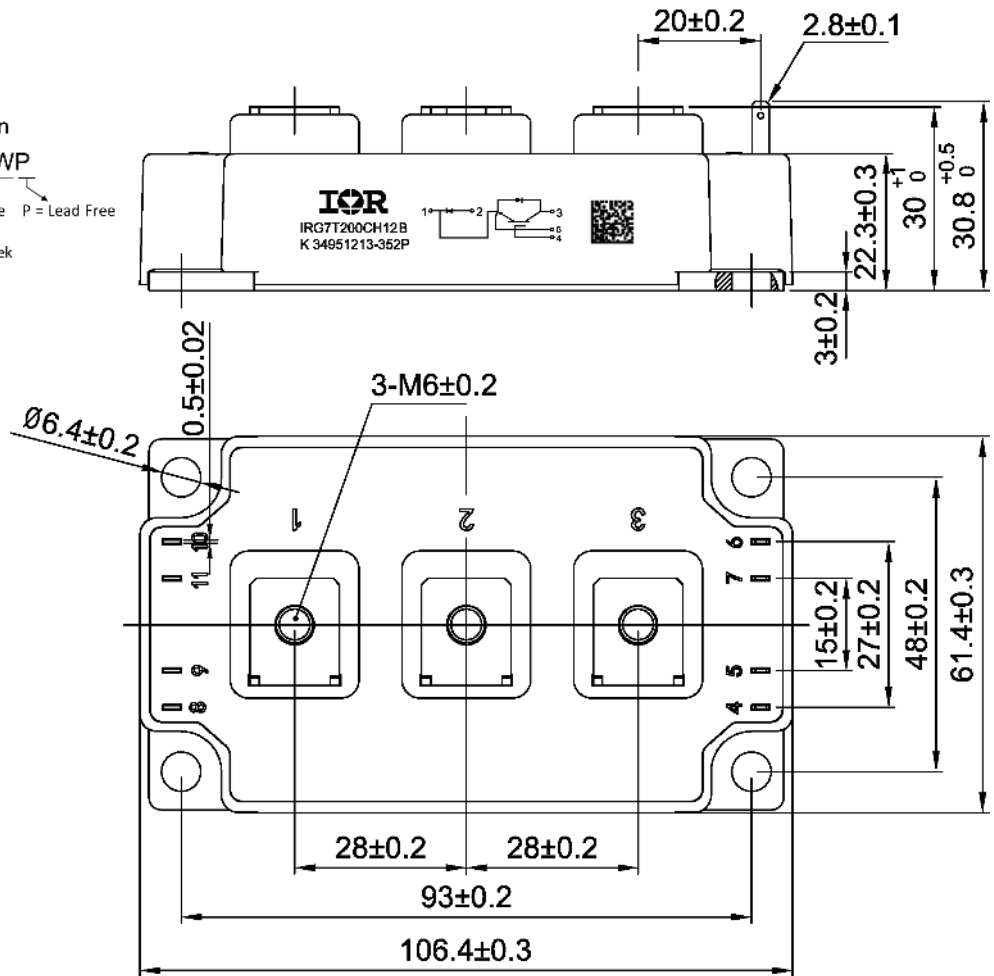
Fig.11 Typical Forward Characteristics, Brake-Chopper Diode

Internal Circuit:



Package Outline (Unit: mm):

Marking Information
K XXXXXXXX-YWWP
Assembly Site Code Lot No. Date Code P = Lead Free
Y = Year
WW = Week



Qualification Information†

Qualification Level	Industrial
Moisture Sensitivity Level	Not Applicable
RoHS Compliant	Yes

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability/>